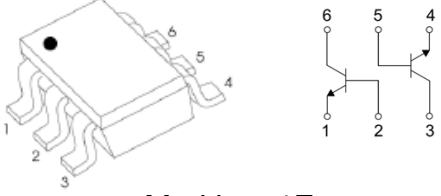


DUAL TRANSISTOR (NPN+NPN)	SOT-363 Plastic-Encapsulate Transistors
<p style="text-align: center;"><u>SOT-363</u></p>  <p style="text-align: center;">Marking :1F</p>	<p style="text-align: center;">Application</p> <p style="text-align: center;">This device is designed for general purpose amplifier applications</p>

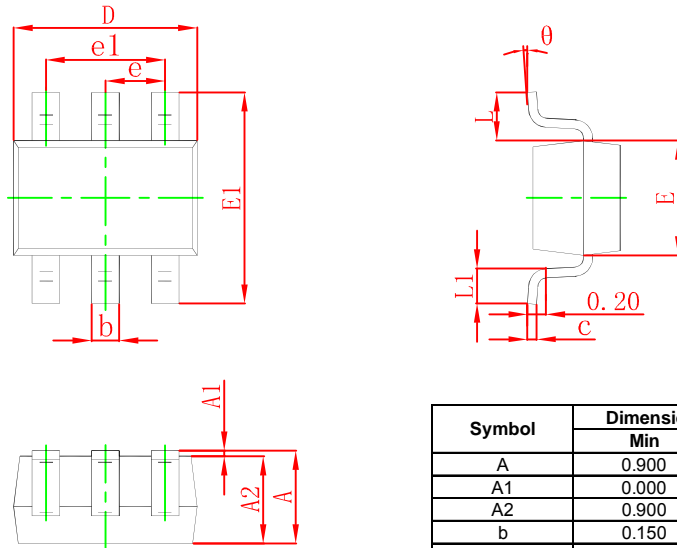
**MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Value	Unit
V <sub>CB0</sub>	Collector-Base Voltage	50	V
V <sub>CEO</sub>	Collector-Emitter Voltage	45	
V <sub>EBO</sub>	Emitter-Base Voltage	6	
I <sub>C</sub>	Collector Current-Continuous	F00	mA
P <sub>D</sub>	Power Dissipation	200	mW
R <sub>θJA</sub>	Thermal Resistance. Junction to Ambient	625	°C/W
T <sub>j</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature Range	-55~+150	

**ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)**

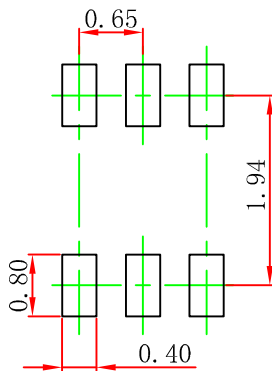
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =10μA, I <sub>E</sub> =0	50			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =1mA, I <sub>B</sub> =0	45			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =10μA, I <sub>C</sub> =0	6			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =30V, I <sub>E</sub> =0			15	nA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =4V, I <sub>C</sub> =0			15	
DC current gain*	h <sub>FE</sub>	V <sub>CE</sub> =5V, I <sub>C</sub> =2mA	110		630	
Collector-emitter saturation voltage	V <sub>CE(sat)(1)</sub>	I <sub>C</sub> =10mA, I <sub>B</sub> =0.5mA			0.25	V
	V <sub>CE(sat)(2)</sub>	I <sub>C</sub> =100mA, I <sub>B</sub> =5mA			0.65	V
Base-emitter voltage	V <sub>BE(1)</sub>	V <sub>CE</sub> =5V, I <sub>C</sub> =2mA	0.58		0.7	V
	V <sub>BE(2)</sub>	V <sub>CE</sub> =5V, I <sub>C</sub> =10mA			0.77	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =5V, I <sub>C</sub> =20mA, f=100MHz		200		MHz
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1MHz		2		pF

**SOT-363 Package Outline Dimensions**



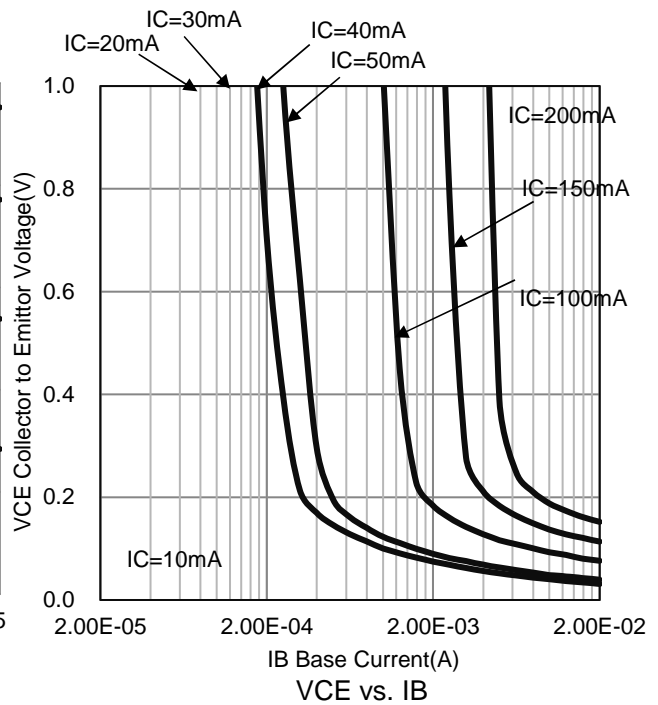
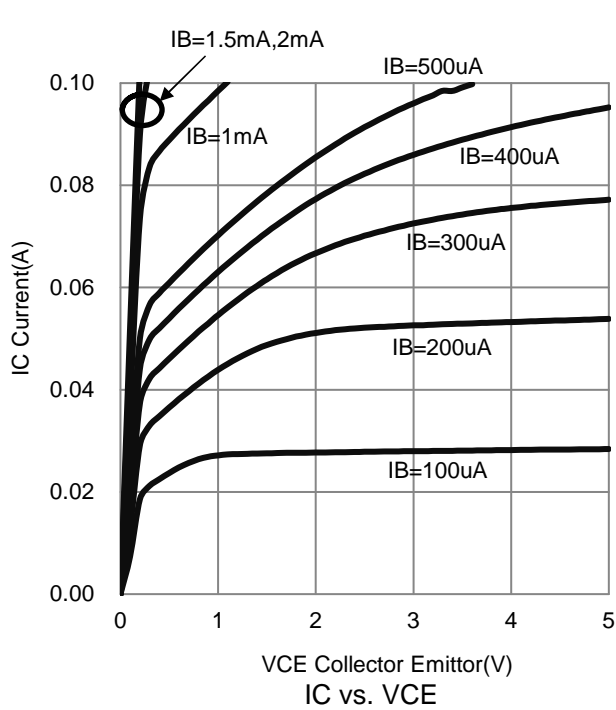
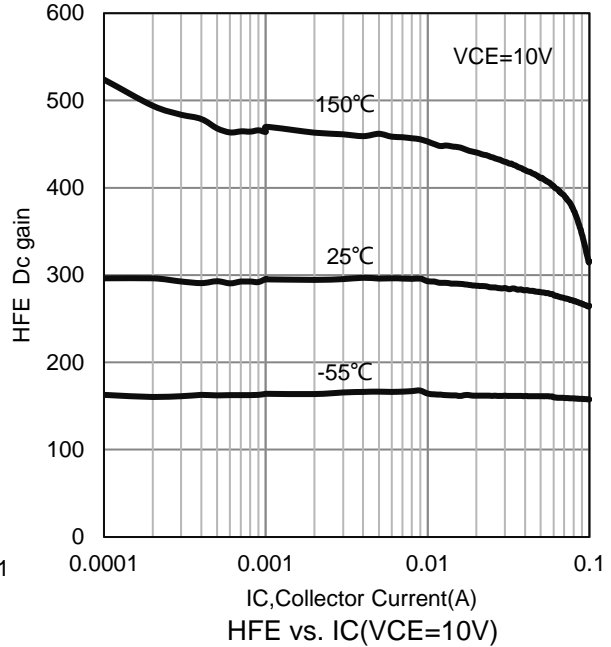
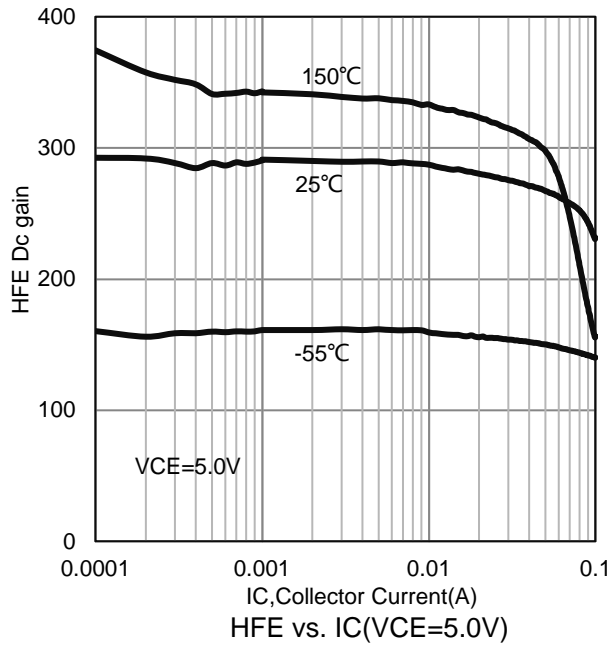
Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.150	0.350	0.006	0.014
c	0.100	0.150	0.004	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.400	0.085	0.094
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
theta	0°	8°	0°	8°

**SOT-363 Suggested Pad Layout**

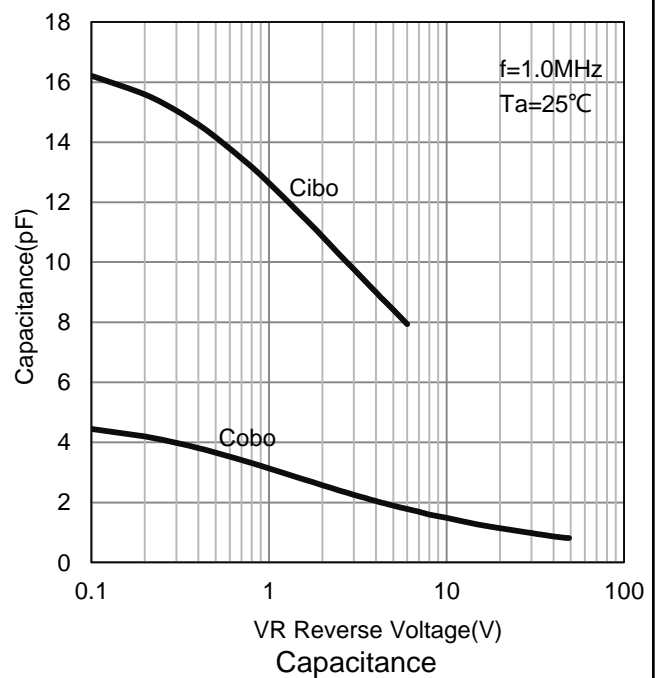
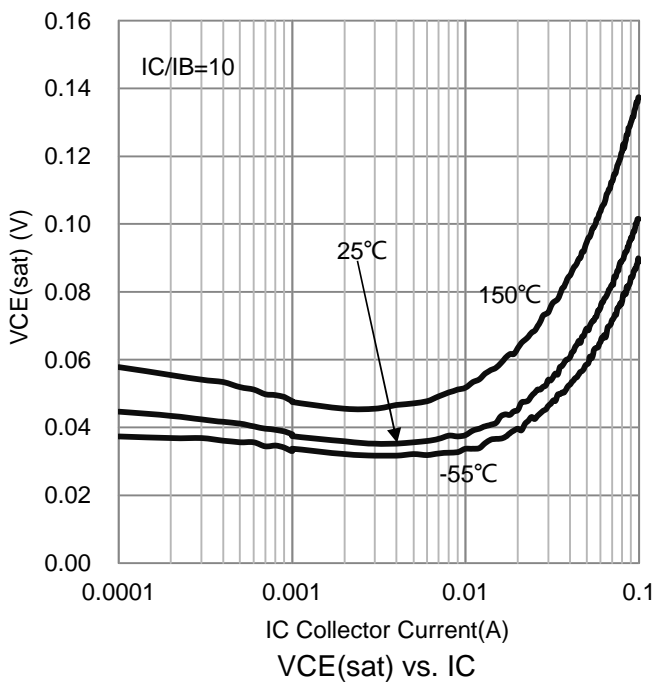
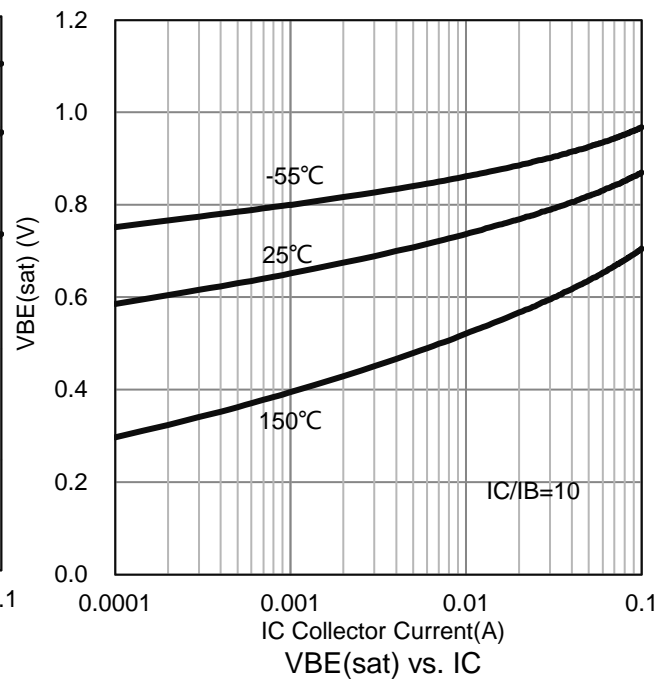
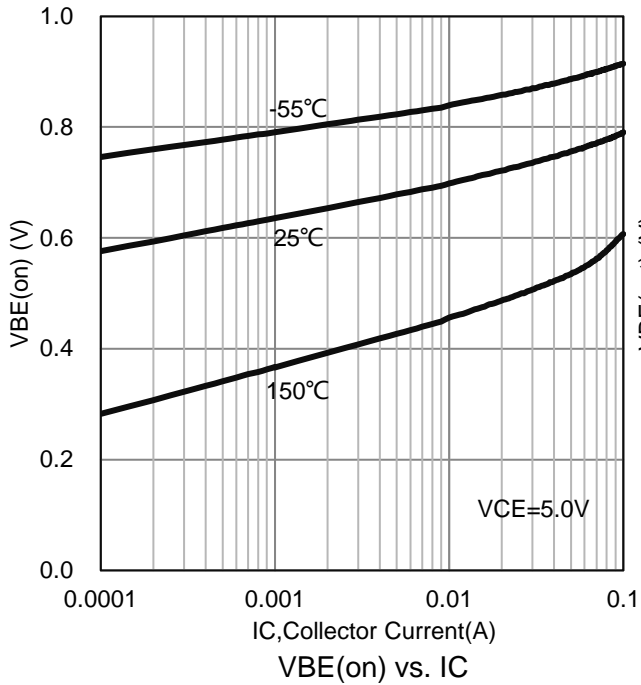


- Note:
1. Controlling dimension: in millimeters.
  2. General tolerance:  $\pm 0.05\text{mm}$ .
  3. The pad layout is for reference purposes only.

**ELECTRICAL CHARACTERISTICS CURVES**



**ELECTRICAL CHARACTERISTICS CURVES(Con.)**



单击下面可查看定价，库存，交付和生命周期等信息

[>>DIOS\(迪恩思\)](#)